

Amendment to the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listings of Claims

Claim 1 (original): A semiconductor device comprising a dielectric layer having a methyl group and exhibiting an SI-H Fourier Transform Infrared (FTIR) doublet defined by a first and a second peak, wherein the first peak is located at a higher wave number than the second peak, and wherein the ratio of the first peak to the second peak is greater than unity.

Claim 2 (original): The semiconductor device as claimed in claim 1, wherein a dielectric constant of the dielectric layer is less than 3.

Claim 3(original): A semiconductor device comprising a dielectric layer having a methyl group and exhibiting a C-H Fourier Transform Infrared (FTIR) peak, an Si-CH₃ FTIR peak, and an SI-H FTIR doublet defined by a first and a second peak, wherein the first peak is located at a higher wave number than the second peak, and wherein the ratio of the first peak to the second peak is greater than unity.

Claim 4 (original): The semiconductor device as claimed in claim 3,
wherein a dielectric constant of the dielectric layer is less than 3.

Claim 5-31 (canceled)